

PATENT ASSIGNMENT

Electronic Version v1.1

Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
Hewlett-Packard Development Company, L.P.	05/18/2007
RECEIVING PARTY DATA	
Name:	Samsung Electronics Co., Ltd.
Street Address:	416 Maetan-dong
Internal Address:	Yeongtong-gu, Suwon-si
City:	Gyeonggi-do
State/Country:	KOREA, REPUBLIC OF
PROPERTY NUMBERS Total: 1	
Property Type	Number
Application Number:	11034418
CORRESPONDENCE DATA	
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ATTORNEY DOCKET NUMBER:	5649-2250
NAME OF SUBMITTER:	Susan E. Freedman
Total Attachments: 30 source=HP_Samsung_Assignment#page1.tif source=HP_Samsung_Assignment#page2.tif source=HP_Samsung_Assignment#page3.tif source=HP_Samsung_Assignment#page4.tif	

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EXHIBIT A
HP PATENT ASSIGNMENT

WHEREAS, Hewlett-Packard Company, a Delaware corporation having a business address at 3000 Hanover Street, Palo Alto, CA 94304-1112 ("**HPCo**") and Hewlett-Packard Development Company, L.P., a Texas limited partnership having a business address at 20555 S.H. 249, Houston, TX 77070 ("**HPDC**", HPCo and HPDC, collectively, "**HP**"), are either the owner or owners, by assignment, of the patents listed in Schedule 1 attached hereto (the "**Assigned Patents**");

AND WHEREAS, Samsung Electronics Co. Ltd., a Korean corporation having a business address at 416 Maetan-dong, Yeongtong-gu, Suwon-si, Gyeonggi-do, Republic of Korea ("**Samsung**") desires to acquire Hewlett-Packard's entire right, title and interest, including the right of priority, in, to and under the Assigned Patents.

NOW, THEREFOR, effective May 18, 2007, HP does hereby assign and transfer to Samsung, HP's entire right, title, and interest in, to and under the Assigned Patents.

HP does hereby grant to Samsung the sole and exclusive right to sue for past infringement of the Assigned Patents, including the right to all past damages. The final decision whether or not a particular party is to be sued lies solely with Samsung. Samsung will have sole control of such suits, shall bear all cost and expenses of such suits and shall be entitled to all proceeds from such suits.

IN WITNESS WHEREOF, HP and Samsung have caused this Assignment to be executed by their authorized representatives.

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HEWLETT-PACKARD COMPANY

SAMSUNG ELECTRONICS CO. LTD.

Signature: Jeffery Fromm

Signature: Jeong Taek Kong

Name: Jeffery Fromm

Name: JEONG-TAEK KONG

Title: VP, Deputy General Counsel,
Intellectual Property

Title: Sr. VP of IP Team

HEWLETT-PACKARD DEVELOPMENT
COMPANY, L.P.

Signature: Jeffery Fromm

By: HPQ Holdings LLC
Its General Partner

Name: Jeffery Fromm

Title: Manager

SCHEDULE 1 **ASSIGNED PATENTS**

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10001383	1 US	6456525	Short-tolerant Resistive Cross Point Array	09/663752	
10001383	6 TW	172120	Short-Tolerant Resistive Cross Point Array	90114989	519643
10001952	1 US	6324093	Write-Once Thin-Film Memory	09/663016	
10001952	4 CN		Write-once Thin-film Memory	01125424.6	1345071
10001952	6 TW	167900	Write-Once Thin-Film Memory	90115268	511089
10001952	7 HK		Write-Once Thin-Film Memory	02107005.6	1045754A
10001952	8 DE	60112860.5	Write-Once Thin-Film Memory	01307834.0	1189239
10001952	9 FR	1189239	Write-Once Thin-Film Memory	01307834.0	1189239
10001952	10 GB	1189239	Write-Once Thin-Film Memory	01307834.0	1189239
10003464	1 US	6317375	Method And Apparatus For Reading Memory Cells Of A Resistive Cross Point Array	09/652807	
10003464	2 JP		Method And Apparatus For Reading Memory Cells Of A Resistive Cross Point Array	P2001-261181	
10003464	4 CN	ZL01132510.0	Method And Apparatus For Reading Memory Cells Of A Resistive Cross Point Array	01132510.0	1345069
10003464	5 KR		Method And Apparatus For Reading Memory Cells Of A Resistive Cross Point Array	2001-0052895	
10003466	1 US	6587384	Multi-Function Serial I/O Circuit	09/839012	20020154536
10003466	2 JP		Multi-function Serial I/O Circuit	P2002-117035	
10003466	3 TW	182261	Multi-Function Serial I/O Circuit	90132234	541531
10003466	4 CN		Multi-function Serial I/O Circuit	02105136.4	1383154
10003466	5 KR		Multi-function Serial I/O Circuit	2002-0021796	
10003466	6 EP		Multi-function Serial I/O Circuit	02252100.9	1251520
10003487	1 US	6429497	Method For Improving Breakdown Voltage In Magnetic Tunnel Junctions	09/715476	
10003487	6 TW	169675	Method For Improving Breakdown Voltage In Magnetic Tunnel Junctions	90115816	512337
10003487	8 DE	60104385.5	Method For Improving Breakdown Voltage In Magnetic Tunnel Junctions	01309220.0	1207538
10003487	9 FR	1207538	Method For Improving Breakdown Voltage In Magnetic Tunnel Junctions	01309220.0	1207538

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HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10003487	10 GB	1207538	Method For Improving Breakdown Voltage In Magnetic Tunnel Junctions	01309220.0	1207538
10003517	2 JP		Method Of Repairing Defective Tunnel Junctions	P2001-279909	
10003517	4 CN	ZL01125891.8	Method Of Repairing Defective Tunnel Junctions	01125891.8	1347118
10003517	5 KR		Method Of Repairing Defective Tunnel Junctions	2001-0060612	
10003517	6 TW	189118	Method Of Repairing Defective Tunnel Junctions	90114614	557525
10003517	7 DE	60107362.2	Method Of Repairing Defective Tunnel Junctions	01308323.3	1195680
10003517	8 GB	1195680	Method Of Repairing Defective Tunnel Junctions	01308323.3	1195680
10003764	1 US	6504779	Resistive Cross Point Memory With On-chip Sense Amplifier Calibration Method And Apparatus	09/855118	20020167838
10003764	2	JP	Resistive Cross Point Memory With On-chip Sense Amplifier Calibration Method And Apparatus	P2002-132918	
10003764	3	CN	Resistive Cross Point Memory With On-chip Sense Amplifier Calibration Method And Apparatus	02119381.9	*
10003989	1 US	6236590	Optimal Write Conductors Layout For Improved Performance In MRAM	09/624134	
10003989	2 JP		Optimal Write Conductors Layout For Improved Performance In MRAM	P2001-221215	2002-118239
10003989	4 CN	ZL01123065.7	Optimal Write Conductors Layout For Improved Performance In MRAM	01123065.7	1338755
10003989	5 KR		Optimal Write Conductors Layout For Improved Performance In MRAM	2001-0043386	
10004243	1 US	6356477	Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	09/771857	
10004243	2 JP		Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	P2002-019411	
10004243	3 CN	ZL01141060.4	Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	01141060.4	1368752
10004243	4 KR		Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	2002-0004803	
10004243	5 TW	173237	Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	90119756	520498
10004243	6 EP		Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	01310636.4	1227495
10004243	7 HK	HK1048703	Cross Point Memory Array Including Shared Devices For Blocking Sneak Path Currents	03100871.1	1048703A
10004574	1 US	6606262	MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) WITH ON-CHIP AUTOMATIC DETERMINATION OF OPTIMIZED WRITE CURRENT METHOD AND APPARATUS	10/044724	20030128578
10004574	2 JP		MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) WITH ON-CHIP AUTOMATIC DETERMINATION OF OPTIMIZED WRITE CURRENT METHOD AND APPARATUS	P2002-342430	*
10004574	3 CN		MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) WITH ON-CHIP AUTOMATIC DETERMINATION OF	03101094.6	1433024 *

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HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10004574	4 KR		OPTIMIZED WRITE CURRENT METHOD AND APPARATUS		
10004574	7 US	6865104	MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) WITH ON-CHIP AUTOMATIC DETERMINATION OF OPTIMIZED WRITE CURRENT METHOD AND APPARATUS	2003-0001331	*
10004574	8 HK		MAGNETORESISTIVE RANDOM ACCESS MEMORY (MRAM) WITH ON-CHIP AUTOMATIC DETERMINATION OF OPTIMIZED WRITE CURRENT METHOD AND APPARATUS	10/459635	20030210596
10004607	1 US	6608790	Write Current Compensation For Temperature Variations In Memory Arrays	04100404.6	1057642A
10004607	2 US	6577549	Write Current Compensation For Temperature Variations In Memory Arrays		
10004607	3 JP		Write Current Compensation For Temperature Variations In Memory Arrays	10/998216	20030103401
10004607	4 CN		Write Current Compensation For Temperature Variations In Memory Arrays	10/254559	20030103402
10004607	5 KR		Write Current Compensation For Temperature Variations In Memory Arrays	P2002-331788	
10005072	1 US	6594171	Memory Systems And Methods Of Making The Same	02154900.1	1423280
10005072	2 JP		Memory Systems And Methods Of Making The Same	2002-0076163	
10005072	3 CN		Memory Systems And Methods Of Making The Same	10/093020	
10005072	4 KR		Memory Systems And Methods Of Making The Same	P2003-059670	
10005072	5 TW	I259557	Memory Systems And Methods Of Making The Same	03119885.6	1444278
10005072	6 EP		Memory Systems And Methods Of Making The Same	2003-0013582	
10005209	1 US	6649423	Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	2003-0013582	
10005209	2 JP		Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	91134113	259557
10005209	3 CN		Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	03251246.9	1343169
10005209	4 KR		Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	09/971347	20030067802
10005209	5 TW	I222063	Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	P2002-278935	
10005209	7 US	6828610	Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	02144497.8	1412863
10005209	8 DE	60203677.1	Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	2002-0060055	
10005209	9 FR	1300853	Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	91119863	222063
				10/626447	20040129928
				02256879.4	1300853
				02256879.4	1300853

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HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10005209	10 GB	1300853	Method For Modifying Switching Field Characteristics Of Magnetic Tunnel Junctions	02256879.4	1300853
10005627	1 US	6848067	Multi-ported Scan Chain Register Apparatus And Method	10/107939	20030188240
10005627	2 JP		Multi-ported Scan Chain Register Apparatus And Method	P2003-087447	
10005627	3 CN		Multi-ported Scan Chain Register Apparatus And Method	03108301.3	1447335
10005627	4 KR		Multi-ported Scan Chain Register Apparatus And Method	2003-0018735	
10005627	7 DE	1349171	Multi-ported Scan Chain Register Apparatus And Method	03251315.2	1349171
10005627	8 GB	1349171	Multi-ported Scan Chain Register Apparatus And Method	03251315.2	1349171
10005726	1 US	6385083	MRAM Device Including Offset Conductors	09/920225	
10005726	2 JP		MRAM Device Including Offset Conductors	P2002-224583	
10005726	3 CN		MRAM Device Including Offset Conductors	02127575.0	1400607
10005726	4 KR		MRAM Device Including Offset Conductors	02-0045172	
10005726	5 TW	191377	MRAM Device Including Offset Conductors	91114865	563127
10006455	1 US	6603678	Information Storage Device Including Heating Elements For Magnetic Memory Elements	09/758757	20020089874
10006455	2 JP		Thermally-Assisted Switching In MRAM Devices	P2001-384427	
10006455	3 CN	ZL01132913.0	Thermally-assisted Switching In MRAM Devices	01132913.0	1365117
10006455	4 KR		Thermally-assisted Switching In MRAM Devices	2002-0001482	
10006455	7 US		Thermally-Assisted Switching In MRAM Devices	10/315748	20030123282
10006455	8 HK	HK1048884	Thermally-assisted Switching In MRAM Devices	03100717.9	1048884
10006455	9 DE	1225592	Thermally-Assisted Switching In MRAM Devices	01310276.9	1225592
10006455	10 GB	1225592	Thermally-Assisted Switching In MRAM Devices	01310276.9	1225592
10006456	1 US	6538920	Cladded Read Conductor For A Pinned-on-the-fly Soft Reference Layer	09/825093	20020186582
10006456	2 JP		Cladded Read Conductor For A Pinned-on-the-fly Soft Referenced Layer	P2002-095681	
10006456	3 TW	182140	Cladded Read Conductor For A Pinned-on-the-fly Soft Referenced Layer	90129843	541529
10006456	4 KR		Cladded Read Conductor For A Pinned-on-the-fly Soft Referenced Layer	2002-0017990	
10006456	7 DE	60201203.1	Cladded Read Conductor For A Pinned-on-the-fly Soft Referenced Layer	02252256.9	1248273
10006456	9 GB	1248273	Cladded Read Conductor For A Pinned-on-the-Fly Soft Referenced Layer	02252256.9	1248273

CONFIDENTIAL

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10006456	10 IT	1248273	Cladded Read Conductor For A Pinned-on-the-fly Soft Referenced Layer	02252256.9	1248273
10006535	1 US	6538917	Read Methods For Magneto-resistive Device Having Soft Reference Layer	09/963851	
10006535	2 JP		Read Methods For Magneto-resistive Device Having Soft Reference Layer	P2002-273429	
10006535	3 CN	ZL02132344.5	Read Methods For Magneto-resistive Device Having Soft Reference Layer	02132344.5	1409321
10006535	4 KR		Read Methods For Magneto-resistive Device Having Soft Reference Layer	2002-0057725	
10006535	5 TW	I263216	Read Methods For Magneto-resistive Device Having Soft Reference Layer	91117781	I263216
10006536	1 US	6576969	Magneto-Resistive Device Having Soft Reference Layer	09/963171	20030058684
10006536	2 JP		Magneto-Resistive Device Having Soft Reference Layer	P2002-273448	
10006536	3 CN		Magneto-resistive Device Having Soft Reference Layer	02132343.7	1466148
10006536	4 KR		Magneto-resistive Device Having Soft Reference Layer	2002-0057732	
10006536	5 TW	I269429	Magneto-resistive Device Having Soft Reference Layer	91117787	
10006536	7 US	6891746	Magneto-Resistive Device Having Soft Reference Layer	10/351013	20030137868
10007010	1 US	6404674	Cladded Read-write Conductor For A Pinned-on-the-fly Soft Reference Layer	09/825461	
10007010	2 JP		Cladded Read-write Conductor For A Pinned-on-the-fly Soft Reference Layer	P2002-095682	
10007010	3 TW	182432	Cladded Read-write Conductor For A Pinned-on-the-fly Soft Reference Layer	090131647	541530
10007010	4 CN		Cladded Read-write Conductor For A Pinned-on-the-fly Soft Reference Layer	02103336.6	1379408
10007010	5 KR		Cladded Read-write Conductor For A Pinned-on-the-fly Soft Reference Layer	2002-0017756	
10007136	1 US	6256247	Differential Sense Amplifiers For Resistive Cross Point Memory Cell Arrays	09/745103	
10007398	1 US	6809958	MRAM Parallel Conductor Orientation For Improved Write Performance	10/243469	20040052104
10007398	2 TW		MRAM Parallel Conductor Orientation For Improved Write Performance	92106095	200405358
10007408	1 US	6475812	Method For Fabricating Cladding Layer In Top Conductor	09/802650	
10007408	2 JP		Method For Fabricating Cladding Layer In Top Conductor	P2002-060538	
10007408	3 KR		Method For Fabricating Cladding Layer In Top Conductor	2002-0012376	
10007408	4 TW	169595	Method For Fabricating Cladding Layer In Top Conductor	90125807	513803
10007408	8 DE	60201036.5	Method For Fabricating Cladding Layer In Top Conductor	02251667.8	1239489
10007408	11 IT	1239489	Method For Fabricating Cladding Layer In Top Conductor	02251667.8	1239489

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10010704	1 US	6657890	Magnetic Memory Device	10/176715	20030235074
10010705	1 US	6747335	Magnetic Memory Cell	10/355787	
10010706	1 US	6982901	Memory Device And Method Of Use	10/355788	
10010706	2 US	7139191	Memory Device And Method Of Use	11/268059	
10010718	1 US	7027092	Image Capture And Storage Device	09/953988	20030052983
10010718	2 JP		Image Capture And Storage Device	P2002-261381	
10010753	1 US	6597597	Low Temperature Attaching Process For MRAM Components	10/053385	20030090931
10010753	2 US	6628543	Low Temperature System For Attaching Magnetoresistive Random Access Memory (As Amended)	10/361097	20030112658
10011012	1 US	6633497	Resistive Cross Point Array Of Short-tolerant Memory Cells	09/887314	20020196647
10011012	2 JP		Resistive Cross Point Array Of Short-tolerant Memory Cells	P2002-179456	
10011012	3 CN		Resistive Cross Point Array Of Short-tolerant Memory Cells	02124896.6	1393887
10011012	4 KR		Resistive Cross Point Array Of Short-tolerant Memory Cells	2002-0034838	
10011012	5 TW	1258214	Resistive Cross Point Array Of Short-tolerant Memory Cells	91108483	
10011293	1 US	6504221	Magneto-Resistive Device Including Soft Reference Layer Having Embedded Conductors	09/963932	
10011293	2 JP		Magneto-Resistive Device Including Soft Reference Layer Having Embedded Conductors	P2002-273428	
10011293	3 CN		Magneto-resistive Device Including Soft Reference Layer Having Embedded Conductors	02132342.9	1409320
10011293	4 KR		Magneto-resistive Device Including Soft Reference Layer Having Embedded Conductors	2002-0057844	
10011293	7 DE	60203675.5	Magneto-resistive Device Including Soft Reference Layer Having Embedded Conductors	02256086.6	1296332
10011293	8 GB	1296332	Magneto-resistive Device Including Soft Reference Layer Having Embedded Conductors	02256086.6	1296332
10011294	1 US	6577529	MULTI- BIT MAGNETIC MEMORY DEVICE	10/235011	
10011294	2 US	6693825	MULTI- BIT MAGNETIC MEMORY DEVICE	10/349685	
10011294	3 JP		MULTI- BIT MAGNETIC MEMORY DEVICE	P2003-311058	
10011294	4 CN		MULTI- BIT MAGNETIC MEMORY DEVICE	03138497.8	1480946
10011294	5 KR		MULTI- BIT MAGNETIC MEMORY DEVICE	2003-0061046	
10011294	6 TW		MULTI- BIT MAGNETIC MEMORY DEVICE	92105948	200405333
10011337	1 US	6639859	Test Array And Method For Testing Memory Arrays	09/983697	20030081477

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10011337	2 JP		Test Array And Method For Testing Memory Arrays	P2002-290178	
10011337	4 KR		Test Array And Method For Testing Memory Arrays	2002-0065107	
10011337	5 TW	192439	Test Array And Method For Testing Memory Arrays	91119697	564433
10011498	1 US	6586989	Nonlinear Digital Differential Amplifier Offset Calibration	10/005456	20030085758
10011498	2 JP		Nonlinear Digital Differential Amplifier Offset Calibration	P2002-322201	
10011752	1 US	6750491	Magnetic Memory Device Having Soft Reference Layer	10/029694	20030117840
10011752	3 CN		Magnetic Memory Device Having Soft Reference Layer	02157854.0	1427416
10011752	4 KR		Magnetic Memory Device Having Soft Reference Layer	2002-0081193	
10011752	7 US	6891212	Magnetic Memory Device Having Soft Reference Layer	10/697191	20040089889
10012432	1 US	7036068	Error Correction Coding And Decoding In A Solid-State Storage Device	09/915194	20030023923
10012432	3 DE		Error Correction Coding And Decoding In A Solid-State Storage Device	10233642.3	
10012438	1 US	6466471	Low Power MRAM Memory Array	09/865596	
10012438	2 JP		Low Power MRAM Memory Array	P2002-155028	
10012438	3 CN		Low Power MRAM Memory Array	02121618.5	1388533
10012493	1 US	6801451	MAGNETIC Memory Devices Having Multiple Bits Per Memory Cell	10/235045	20040042264
10012493	3 CN		MAGNETIC Memory Devices Having Multiple Bits Per Memory Cell	03136378.4	1492443
10012493	4 KR		MAGNETIC Memory Devices Having Multiple Bits Per Memory Cell	2003-0060984	
10012493	7 HK		MAGNETIC Memory Devices Having Multiple Bits Per Memory Cell	04105735.5	1062954A
10012496	1 US	6385079	Methods And Structure For Maximizing Signal To Noise Ration In Resistive Array	09/944680	
10012496	2 JP		Methods And Structure For Maximizing Signal To Noise Ration In Resistive Array	P2002-252879	
10012496	3 CN		Methods And Structure For Maximizing Signal To Noise Ration In Resistive Array	02141490.4	1407557
10012496	4 KR		Methods And Structure For Maximizing Signal To Noise Ration In Resistive Array	2002-0052194	
10013804	1 US		MRAM With Controller	10/743662	20050135165
10013884	1 US	6906947	In-Plane Toroidal Memory Cell With Vertically Stepped Conductors	10/080847	20030161179
10013887	1 US	6661688	Method And Article For Concentrating Fields At Sense Layers	10/005423	20030104636
10013887	2 US	6791872	Method And Article For Concentrating Fields At Sense Layers	10/652446	20040042302

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10013887	3 US	6791857	Method And Article For Concentrating Fields At Sense Layers	10/668442	20040057303
10014151	1 US	6834017	Error Detection System For An Information Storage Device	10/264588	20040066690
10014155	1 US	6944053	Magnetic Memory With Structure Providing Reduced Coercivity (As Amended)	10/462979	20040257867
10014155	2 US	7187580	Magnetic Memory With Structure Providing Reduced Coercivity	11/222623	20060002183
10014168	1 US	6870758	Magnetic Memory Device And Methods For Making Same	10/283559	20040085808
10014168	2 JP		Magnetic Memory Device And Methods For Making Same	P2003-361588	
10014168	3 US		Magnetic Memory Device And Methods For Making Same	11/021268	20050111254
10014177	1 US	6646910	Magnetic Memory Using Reverse Magnetic Field To Improve Half-Select Margin	10/090246	20030174537
10014181	1 US	6643213	Write Pulse Circuit For A Magnetic Memory	10/096542	20030174574
10014197	1 US	6775196	Magnetic Memory Having A Temperature Compensated Write Circuit	10/194767	20040008557
10014201	1 US	6650562	System And Method For Determining The Logic State Of A Memory Cell In A Magnetic Tunnel Junction Memory Device	10/055299	20030137864
10014201	2 JP		System And Method For Determining The Logic State Of A Memory Cell In A Magnetic Tunnel Junction Memory Device	P2003-013288	
10014201	4 US	6999334	System And Methods For Determining The Logic State Of A Memory Cell In A Magnetic Tunnel Junction Memory Device	10/660831	20050099855
10014202	1 US	6762952	Minimizing Errors In A Magnetoresistive Solid-State Storage Device	10/138074	20030206432
10014202	2 JP		Minimizing Errors In A Magnetoresistive Solid-State Storage Device	P2003-126443	
10014202	3 FR	0304960	Minimizing Errors In A Magnetoresistive Solid-State Storage Device	0304960	2839380
10014203	1 US	6678200	Systems And Methods For Communicating With Memory Blocks	10/145834	20030214869
10014203	2 KR		Systems And Methods For Communicating With Memory Blocks	2003-0030326	
10014203	3 GB	2392327	Systems And Methods For Communicating With Memory Blocks	0309921.5	2392327
10014203	4 US	6842390	Systems And Methods For Communicating With Memory Blocks	10/675191	20040066691
10014203	5 GB	2409776	Systems And Methods For Communicating With Memory Blocks	0506805.1	2409776
10014207	1 US	6678197	Systems And Methods For Reducing The Effect Of Noise While Reading Data From Memory	10/273623	
10014216	1 US	6717874	Systems And Methods For Reducing The Effect Of Noise While Reading Data In Series From Memory	10/218892	
10014219	1 US	6990030	Magnetic Memory Having A Calibration System	10/690249	20050083748
10014219	2 DE		Magnetic Memory Having A Calibration System	102004030543.9	102004030543 *

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no	
10014219	3 TW		Magnetic Memory Having A Calibration System	93111602	200515413	*
10014224	1 US		Magnetic Memory Which Compares Compressed Fault Maps	10/722918	20050138495	
10014224	2 GB	GB2408603	Integrated Circuit Type Magnetic Memory With Error Correction (as Amended)	0425055.1	2408603	
10014228	1 US		Magnetic Memory	10/700203	20050094459	
10014230	1 US	6826094	Magnetic Memory Cell Sensing With First And Second Currents	10/452755	20040240276	
10014230	3 GB	GB2402823	Magnetic Memory Cell Sensing With First And Second Currents	0411144.9	2402823	
10014232	1 US	6900491	Magnetic Memory	10/679564	20050072995	
10014232	2 DE		Magnetic Memory	102004030592.7	102004030592	
10014243	1 US	6728153	Magnetic Memory Which Compares First Memory Cell Data Bits And Second Data Bits	10/223490	20040032777	
10014269	1 US	6765819	Magnetic Memory Device Having Improved Switching Characteristics	10/205531		
10014272	1 US	6865107	Magnetic Memory Device	10/601895	20040257870	
10014272	2 FR	0406159	Magnetic Memory Device	0406159	2856508	
10014272	3 KR		Magnetic Memory Device	2004-0046438		
10014277	1 US	6724027	Magnetic Shielding For MRAM Devices	10/125095	20030197211	
10014281	1 US		Data Storage System With Error Correction Code And Replaceable Defective Memory	10/725855	20050120265	
10014281	2 TW		Data Storage System With Error Correction Code And Replaceable Defective Memory	93118072		
10014281	4 GB		Data Storage System With Error Correction Code And Replaceable Defective Memory	0610937.5	2423848	
10014296	1 US	7057249	Magnetic Memory Device	10/612676	20050001249	
10014296	2 JP		Magnetic Memory Device	P2004-195151		
10014298	1 US	6940153	Magnetic Shielding For Magnetic Random Access Memory Card	10/358770	20040152261	
10014298	3 TW		Magnetic Shielding For Magnetic Random Access Memory Card	92122591		*
10014298	4 GB	GB2398174	Magnetic Shielding For Magnetic Random Access Memory Card	0400870.2	2398174	
10014298	5 US		Method Of Packaging Magnetic Memory (As Amended)	11/203755	20060044929	
10014319	1 US	6564742	Over-Temperature Warning Device	09/921145	20030024465	
10014319	3 CN	ZL02127549.2	Over-Temperature Warning Device	02127459.2	1405539	
10014319	4 KR		Over-temperature Warning Device	02.0045823		

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10014319	5 TW	199886	Over-Temperature Warning Device	91114862	581861
10014319	6 EP		Over-temperature Warning Device	02254917.4	1281946
10014331	1 US	6911710	Multibit Magnetic Memory Cells	09/925755	20020036331
10014331	3 CN		Multibit Magnetic Memory Cells	02128645.0	1405777
10014331	4 KR		Multibit Magnetic Memory Cells	02.0046840	
10014331	7 US	6862212	Multi-bit Magnetic Memory Cells	10/697172	20040090844
10014430	1 US	6754097	Read Operations On Multi-bit Memory Cells In Resistive Cross Point Arrays	10/234511	20040042263
10014430	2 JP		Read Operations On Multi-bit Memory Cells In Resistive Cross Point Arrays	P2003-310899	
10014430	3 CN		Read Operations On Multi-bit Memory Cells In Resistive Cross Point Arrays	03145804.1	1516187
10014430	4 TW		Read Operations On Multi-bit Memory Cells In Resistive Cross Point Arrays	92106378	
10014430	6 HK		Read Operations On Multi-bit Memory Cells In Resistive Cross Point Arrays	04109037.2	1066319A
10015162	1 US	6515896	Memory Device With Short Read Time	09/910823	20030021145
10015162	2 JP		Memory Device With Short Read Time	P2002-207874	
10015162	3 CN	ZL02126952.1	Memory Device With Short Read Time	02126952.1	1399276
10015162	4 KR		Memory Device With Short Read Time	02-0043145	
10015162	5 TW	222062	Memory Device With Short Read Time	91112535	222062
10015175	1 US	6501697	High Density Memory Sense Amplifier	09/976304	
10015175	3 CN		High Density Memory Sense Amplifier	02143597.9	1412777
10015175	4 KR		High Density Memory Sense Amplifier	2002-0061770	
10015175	5 TW	I240282	High Density Memory Sense Amplifier	91119524	240282
10015175	7 DE	60205193.2	High Density Memory Sense Amplifier	02256366.2	1302948
10015175	8 GB	1302948	High Density Memory Sense Amplifier	02256366.2	1302948
10015434	1 US	6462388	Isolation Of Memory Cells In Cross Point Arrays	09/912565	
10015434	2 JP		Isolation Of Memory Cells In Cross Point Arrays	P2002-212807	
10015434	4 KR		Isolation Of Memory Cells In Cross Point Arrays	02-0043769	*
10015434	6 EP		Isolation Of Memory Cells In Cross Point Arrays	02254672.5	1280209

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10015599	1 US	6772277	Method Of Writing To A Memory Array Using Clear Enable And Column Clear Signals (as Amended)	09/845387	20020161964
10015599	2 FR	0205428	Method Of Writing To A RAM With Column Clear	0205428	2828758
10015599	3 JP		Method Of Writing To A RAM With Column Clear	P2002-123589	
10015599	4 DE		Method Of Writing To A RAM With Column Clear	10217290.0	10217290
10016258	1 US	7186992	Method Of Fabricating A Polarizing Layer On An Interface	11/053381	20060177594
10016259	1 US		Method Of Fabricating A Manganese Diffusion Barrier	11/050273	20060172086
10016604	1 US	6597049	CONDUCTOR STRUCTURE FOR A MAGNETIC MEMORY	10/132998	
10016604	2 JP		CONDUCTOR STRUCTURE FOR A MAGNETIC MEMORY	P2003-116650	
10016604	3 CN		CONDUCTOR STRUCTURE FOR A MAGNETIC MEMORY	03122470.9	1453791
10016604	4 KR		CONDUCTOR STRUCTURE FOR A MAGNETIC MEMORY	2003-0025986	
10016604	5 TW		CONDUCTOR STRUCTURE FOR A MAGNETIC MEMORY	91137056	
10017400	1 US	6570782	Storage And Retrieval For Resistance-Based Memory Devices	10/050668	
10017408	1 US	6937509	Data Storage Device And Method Of Forming The Same	10/657385	20050052893
10017408	2 KR		Data Storage Device And Method Of Forming The Same	2004-0071054	*
10017408	4 US	7031185	Data Storage Device And Method Of Forming The Same	11/171694	20050237845
10017901	1 US	6504742	3-D Memory Device For Large Storage Capacity	09/984934	
10017901	4 KR		3-D Memory Device For Large Storage Capacity	2002-0066377	
10017901	7 DE	60208310.9	3-D Memory Device For Large Storage Capacity	02257425.5	1308958
10017901	8 GB	1308958	3-D Memory Device For Large Storage Capacity	02257425.5	1308958
10018141	1 US	6826077	Magnetic Random Access Memory With Reduced Parasitic Currents	10/146201	20030214837
10018141	3 DE		Magnetic Random Access Memory With Reduced Parasitic Currents	10312677.5	10312677
10018461	1 US	6968479	Verifying Data In A Data Storage Device	10/092111	20030172325
10019196	1 US	6795281	Magneto-Resistive Device Including Soft Synthetic Ferrimagnet Reference Layer	09/963933	20030057461
10019196	2 JP		Magneto-Resistive Device Inc. Soft Synthetic Ferrimagnet Reference Layer	P2002-273449	
10019287	1 US	6466475	Uniform Magnetic Environment For Cells In An MRAM Array	10/000652	
10019287	2 JP		Uniform Magnetic Environment For Cells In An MRAM Array	P2002-311295	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no	
10019665	1 US	6781578	Stylus Based Input Devices Utilizing A Magnetic Random Access Memory Array	10/038485	20030122790	
10019666	1 US	6798404	An Integrated Digitizing Tablet And Display Appartus And Method Of Operation	10/038466	20030122789	
10019666	4 KR		An Integrated Digitizing Tablet And Display Appartus And Method Of Operation	2003-0000095		
10970365	1 US		Solid-State Memory With Magnetic Storage Cells	08/974925		
10970365	4 US	6169686	Solid-state Memory With Magnetic Storage Cells	08/974925		
10970365	5 US		Solid-state Memory With Magnetic Storage Cells	09/561317		
10970365	6 US	6607924	Solid State Memory With Magnetic Storage Cells	09/871387	20020013004	
10970365	8 US	6424565	Solid-state Memory With Magnetic Storage Cells	09/561317	20020003721	
10971256	1 US	6301186	RAM Cell With Column Clear	09/845383		
10971653	1 US	6169303	Ferromagnetic Tunnel Junctions With Enhanced Magneto-resistance	09/003320		
10971653	4 CN	ZL98122589.6	Ferromagnetic Tunnel Junctions With Enhanced Magneto-resistance	98122589.6	1222771	
10971653	5 US		Ferromagnetic Tunnel Junctions With Enhanced Magneto-resistance	09/672794		*
10971653	6 US	6511855	Ferromagnetic Tunnel Junctions With Enhanced Magneto-resistance	09/672794	20020114972	
10971653	7 DE	69913574.5	Ferromagnetic Tunnel Junctions With Enhanced Magneto-resistance	99300005.8	0929110	
10971653	9 GB	0929110	Ferromagnetic Tunnel Junctions With Enhanced Magneto-resistance	99300005.8	0929110	
10980881	1 US	6072717	Stabilized Magnetic Memory Cell	09/146819		
10980881	2 JP		Stabilized Magnetic Memory Cell	PH11-247566		
10980881	4 CN	ZL99111947.9	Stabilized Magnetic Memory Cell	99111947.9	1247367	
10980881	5 US	6205051	Stabilized Magnetic Memory Cell	09/522269		
10980901	1 US	6081446	Multiple Bit Magnetic Memory Cell	09/089947		
10980901	4 CN	ZL99106982.X	Multiple Bit Magnetic Memory Cell	99106982.X	1237766	*
10980931	1 US	5982660	Magnetic Memory Cell With Off Axis Reference Layer Orientation For Improved Response	09/140992		
10981641	1 US	6097626	MRAM Device Using Magnetic Field Bias To Suppress Inadvertent Switching Of Half-Selected Memory Cells	09/363082		
10981641	2 JP		MRAM Device Using Magnetic Field Bias To Suppress Inadvertent Switching Of Half-Selected Memory Cells	P2000-228117		
10981641	3 EP	1073062	MRAM Device Using Magnetic Field Bias To Suppress Inadvertent Switching Of Half-Selected Memory Cells	00306378.1	1073062	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no	
10981641	4 DE	1073062	MRAM Device Using Magnetic Field Bias To Suppress Inadvertent Switching Of Half-Selected Memory Cells	00306378.1	1073062	
10981641	5 FR	1073062	MRAM Device Using Magnetic Field Bias To Suppress Inadvertent Switching Of Half-Selected Memory Cells	00306378.1	1073062	
10981641	6 GB	1073062	MRAM Device Using Magnetic Field Bias To Suppress Inadvertent Switching Of Half-Selected Memory Cells	00306378.1	1073062	
10981733	1 US	6172904	Magnetic Memory Cell With Symmetric Switching Characteristics	09/492260		
10981733	2 JP		Magnetic Memory Cell With Symmetric Switching Characteristics	P2001-019744	2001-267523	
10981733	3 EP	1126469	Magnetic Memory Cell With Symmetric Switching Characteristics	00311117.6	1126469	
10981733	4 DE	60022616.6	Magnetic Memory Cell With Symmetric Switching Characteristics	00311117.6	1126469	
10981733	5 FR	1126469	Magnetic Memory Cell With Symmetric Switching Characteristics	00311117.6	1126469	
10981733	6 GB	1126469	Magnetic Memory Cell With Symmetric Switching Characteristics	00311117.6	1126469	
10981879	1 US	6111783	MRAM Device Including Write Circuit For Supplying Word And Bit Line Current Having Unequal Magnitudes	09/334485		
10982050	1 US	6317376	Reference Signal Generation For MRAM Devices	09/598671		
10982050	4 CN	ZL01121930.0	Reference Signal Generation For Magnetic Random Access Memory (MRAM) Devices	01121930.0	1337709	*
10982050	7 US	6385111	Reference Signal Generation For Magnetic Random Access Memory Devices	09/809707	20010053104	
10982370	1 US	6728799	Hybrid Data I/O For Memory Applications	09/483383		
10982370	2 JP		Hybrid Data I/O For Memory Applications	P2001-004951	2001-229688	
10982377	1 US	6128239	MRAM Device Including Analog Sense Amplifiers	09/430239		
10982377	2 JP		MEMORY CELL RSISTANCE STATE SENSING	P2000-325971		
10990021	1 US	6163477	MRAM Device Using Magnetic Field Bias To Improve Reproducibility Of Memory Cell Switching	09/370087		
10990021	2 JP		MRAM Device Using Magnetic Field Bias To Improve Reproducibility Of Memory Cell Switching	P2000-235407		
10990021	4 DE	1074992	MRAM Device Using Magnetic Field Bias To Improve Reproducibility Of Memory Cell Switching	00306285.8	1074992	
10990021	5 FR	1074992	MRAM Device Using Magnetic Field Bias To Improve Reproducibility Of Memory Cell Switching	00306285.8	1074992	
10990021	6 GB	1074992	MRAM Device Using Magnetic Field Bias To Improve Reproducibility Of Memory Cell Switching	00306285.8	1074992	
10990034	4 US	6358757	Magnetic Memory With Structures That Prevent Disruptions To Magnetization In Sense Layers	09/824810		

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10990108	1 US	6297983	Improved Reference Layer Structure In A Magnetic Storage Cell	09/514961	
10990108	2 JP		Improved Reference Layer Structure In A Magnetic Storage Cell	P2001-051626	2001-308292
10990108	4 US	6479353	Reference Layer Structure In A Magnetic Storage Cell	09/871395	
10990108	5 HK	HK1036144	Improved Reference Layer Structure In A Magnetic Storage Cell	01107057.4	1036144
10990216	1 US	6590806	Multibit Magnetic Memory Element	09/522308	
10990216	2 JP		Multibit Magnetic Memory Element	P2001-066411	2001-313377
10990216	3 GB	1132919	Memory Cell	01301747.0	1132919
10990216	3 DE	60301097	Memory Cell	01301747.0	1132919
10990216	4 CN		Multibit Magnetic Memory Element	01111226.3	1316746
10990216	5 TW	169555	Multibit Magnetic Memory Element	90102977	514914
10990216	7 HK		Multibit Magnetic Memory Element	02102604.2	1041098A
10990233	1 US	6205053	Magnetically Stable Magnetoresistive Memory Element	09/597958	
10990233	2 JP		Magnetically Stable Magnetoresistive Memory Element	P2001-157177	2002-056665
10990233	6 TW	168220	Magnetically Stable Magnetoresistive Memory Element	90110481	512335
10990326	1 US	6185143	MRAM Device Including Differential Sense Amplifiers	09/498587	
10990326	2 JP		MRAM Device Including Differential Sense Amplifiers	P2001-028596	2001-273756
10990326	3 EP	1126468	MRAM Device Including Differential Sense Amplifiers	00122074.8	1126468
10990326	4 CN		MRAM Device Including Differential Sense Amplifiers	00133877.3	1319846
10990326	6 DE	60025152.7	MRAM Device Including Differential Sense Amplifiers	00122074.8	1126468
10990326	8 GB	1126468	MRAM Device Including Differential Sense Amplifiers	00122074.8	1126468
10990327	1 US	6584589	Self-Testing Of Magneto-Resistive Memory Arrays	09/498588	
10990327	2 JP		Self-Testing Of Magneto-Resistive Memory Arrays	P2001-028595	2001-273799
10990327	4 CN	ZL00132356.3	Self-Testing Of Magneto-Resistive Memory Arrays	00132356.3	1317797
10990327	5 HK		Self-Testing Of Magneto-Resistive Memory Arrays	02102603.3	1041361A
10990673	1 US	6259644	Equipotential Sense Methods For Resistive Cross Point Memory Cell Arrays	09/564308	
10990673	4 CN	ZL01117937.6	Equipotential Sense Methods For Resistive Cross Point Memory Cell Arrays	01117937.6	1327238

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
10990742	1 US	6134139	Magnetic Memory Structure With Improved Half-select Margin	09/363081	
10990742	2 JP		Magnetic Memory Structure With Improved Half-Select Margin	P2000-220088	2001-044379
10990992	1 US	6188615	MRAM Device Including Digital Sense Amplifiers	09/430611	
10990992	2 JP	3760092	MRAM Device Including Digital Sense Amplifiers	P2000-330455	2001-184857
10990992	6 DE	60018875.2	MRAM Device Including Digital Sense Amplifiers	00309341.6	1096501
10990992	7 FR	1096501	MRAM Device Including Digital Sense Amplifiers	00309341.6	1096501
10990992	8 GB	1096501	MRAM Device Including Digital Sense Amplifiers	00309341.6	1096501
10990999	1 US	6262625	Operational Amplifier With Digital Offset Calibration	09/430238	
10990999	2 JP		Operational Amplifier With Digital Offset Calibration	P2000-329103	
10991744	1 US	6727105	Method Of Fabricating An MRAM Device Including Spin Dependent Tunneling Junction Memory Cells	09/514934	
10991744	2 JP		Method Of Fabricating An MRAM Device Including Spin Dependent Tunneling Junction Memory Cells	P2001-047766	2001-298228
10991744	4 US	6885049	MRAM Device Including Spin Dependent Tunneling Junction Memory Cells (title Amended)	09/981277	20020047145
10992726	1 US	6256224	Write Circuit For Large MRAM Arrays	09/564713	
10992726	2 JP		Write Circuit For Large MRAM Arrays	P2001-134426	2002-8368
10992726	4 KR		Write Circuit For Large MRAM Arrays	2001-0023745	
10992726	5 CN		Write Circuit For Large MRAM Arrays	01117942.2	1329336
10992726	7 US	6363000	Write Circuit For Large MRAM Arrays	09/827114	20010038548
30011232	1 US	6981196	Data Storage Method For Use In A Magnetoresistive Solid-State Storage Device	09/915195	20030023924
30011232	2 JP		Data Storage Method For Use In A Magnetoresistive Solid-State Storage Device	P2002-216149	
30018671	1 US	6973604	Allocation Of Sparing Resources In A Magnetoresistive Solid-state Storage Device	10/093833	20030172329
30018672	1 US	7107507	Magnetoresistive Solid-state Storage Device And Data Storage Methods For Use Therewith	10/093832	
30018673	1 US	7107508	Manufacturing Test For A Fault Tolerant Magnetoresistive Solid-state Storage Device	10/093851	
30018674	1 US	6990622	Method For Error Correction Decoding In An MRAM Device (Historical Erasures)	10/093854	
30990090	4 US	6549446	Data Balancing Scheme In Solid State Storage Devices	09/959591	20020159285
100110111	1 US	6781910	Small Area Magnetic Memory Devices	10/147597	20030214838
100110111	2 JP		Small Area Magnetic Memory Devices	P2003-131176	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
100110390	1 US	6507513	Using Delayed Electrical Pulses With Magneto-resistive Devices	10/176179	
100110390	3 CN		Using Delayed Electrical Pulses With Magneto-Resistive Devices	03142472.4	1469385
100110390	4 KR		Using Delayed Electrical Pulses With Magneto-Resistive Devices	2003-0039649	
100110391	1 US	6625059	Synthetic Ferrimagnet Reference Layer For A Magnetic Storage Device	10/093344	20030169620
100110391	2 JP		Synthetic Ferrimagnet Reference Layer For A Magnetic Storage Device	P2003-058137	
100110391	3 CN		Synthetic Ferrimagnet Reference Layer For A Magnetic Storage Device	03119936.4	1442861
100110391	4 KR		Synthetic Ferrimagnet Reference Layer For A Magnetic Storage Device	2003-0013710	
100110391	5 TW		Synthetic Ferrimagnet Reference Layer For A Magnetic Storage Device	91134208	
100110467	1 US	6850433	A Magnetic Memory Device And Method	10/196877	20040008537
100110467	2 JP		A Magnetic Memory Device And Method	P2003-186790	
100110467	3 CN		A Magnetic Memory Device And Method	03136044.0	1487524
100110467	4 TW		A Magnetic Memory Device And Method	92104568	
100110627	1 US	6803616	Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	10/173195	20030231520
100110627	2 JP		Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	P2003-171478	
100110627	3 CN		Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	03123133.0	1469384
100110627	4 KR		Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	2003-0038615	
100110627	5 TW		Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	91137048	
100110627	7 US	6905888	Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	10/676414	20040062125
100110627	9 DE	60301097.0	Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	03253059.4	1376600
100110627	10 GB	1376600	Magnetic Memory Element Having Controlled Nucleation Site In Data Layer	03253059.4	1376600
100111370	1 US	6778421	Memory Device Array Having A Pair Of Magnetic Bits Sharing A Common Conductor Line	10/098903	20030174530
100111370	2 JP		Memory Device Array Having A Pair Of Magnetic Bits Sharing A Common Conductor Line	P2003-069239	
100111370	3 CN		Memory Device Array Having A Pair Of Magnetic Bits Sharing A Common Conductor Line	03119972.0	1445782
100111370	4 KR		Memory Device Array Having A Pair Of Magnetic Bits Sharing A Common Conductor Line	2003-0015743	
100111370	5 TW		Memory Device Array Having A Pair Of Magnetic Bits Sharing A Common Conductor Line	91134207	
100111370	7 US	6879508	Memory Device Array Having A Pair Of Magnetic Bits Sharing A Common Conductor Line	10/692617	20040090809

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
100111375	1 US	6678189	Method And System For Performing Equipotential Sensing Across A Memory Array To Eliminate Leakage Currents	10/084111	20030161178
100111375	2 JP		Method And System For Performing Equipotential Sensing Across A Memory Array To Eliminate Leakage Currents	P2003-044349	
100111375	3 CN		Method And System For Performing Equipotential Sensing Across A Memory Array To Eliminate Leakage Currents	03106348.9	1444228
100111375	4 KR		Method And System For Performing Equipotential Sensing Across A Memory Array To Eliminate Leakage Currents	2003-0011268	
100111375	5 TW		Method And System For Performing Equipotential Sensing Across A Memory Array To Eliminate Leakage Currents	92100628	
100111375	7 US	6826079	Method And System For Performing Equipotential Sensing Across A Memory Array To Eliminate Leakage Currents	10/459437	20030206473
100111472	1 US	6757188	Triple Sample Sensing For Magnetic Random Access Memory (MRAM) With Series Diodes	10/151915	20030218902
100111472	2 JP		Triple Sample Sensing For Magnetic Random Access Memory (MRAM) With Series Diodes	P2003-137360	
100111472	3 CN		Triple Sample Sensing For Magnetic Random Access Memory (MRAM) With Series Diodes	03108328.5	1459792
100111472	4 KR		Triple Sample Sensing For Magnetic Random Access Memory (MRAM) With Series Diodes	2003-0032168	
100111472	5 TW		Triple Sample Sensing For Magnetic Random Access Memory (MRAM) With Series Diodes	91136378	
100111472	7 US	6873544	Triple Sample Sensing For Magnetic Random Access Memory (MRAM) With Series Diodes	10/696826	20040090841
100111473	1 US	6801450	Memory Cell Isolation	10/151914	20030218906
100111473	4 KR		Memory Cell Isolation	2003-0032166	
100111489	1 US	6794695	MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	10/135241	20030202375
100111489	2 JP		MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	P2003-120171	
100111489	3 CN		MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	03120147.4	1455463
100111489	4 KR		MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	2003-0026705	
100111489	6 EP	1359590	MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	03252587.5	1359590
100111489	7 US	6919594	MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	10/696991	20040090842
100111489	8 DE	60301294.9	MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	03252587.5	1359590
100111489	9 GB	1359590	MAGNETO RESISTIVE STORAGE DEVICE HAVING A MAGNETIC FIELD SINK LAYER	03252587.5	1359590
100111530	1 US	6927996	A Magnetic Memory Device	10/676465	20050068830
100111542	1 US		Increased Magnetic Memory Array Sizes And Operating Margins	10/661448	20050094458

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
100111590	1 US	6885573	Improved Diode For Use In MRAM Devices And Method Of Manufacture	10/098206	20030185038
100111590	2 JP		Improved Diode For Use In MRAM Devices And Method Of Manufacture	P2003-065876	
100111590	3 CN		Improved Diode For Use In MRAM Devices And Method Of Manufacture	03119976.3	
100111590	4 KR		Improved Diode For Use In MRAM Devices And Method Of Manufacture	2003-0016019	
100111590	5 TW		Improved Diode For Use In MRAM Devices And Method Of Manufacture	92103544	
100111591	1 US	6593608	Magneto Resistive Storage Device Having A Double Tunnel Junction	10/098204	
100111591	2 JP		Magneto Resistive Storage Device Having A Double Tunnel Junction	P2003-065875	
100111591	3 CN		Magneto Resistive Storage Device Having A Double Tunnel Junction	03119964.X	1445781
100111591	4 KR		Magneto Resistive Storage Device Having A Double Tunnel Junction	2003-0016054	
100111591	5 TW		Magneto Resistive Storage Device Having A Double Tunnel Junction	91134205	
100111620	1 US	6597598	Resistive Cross Point Memory Arrays Having A Charge Injection Differential Sense Amplifier	10/136782	
100111620	2 JP		Resistive Cross Point Memory Arrays Having A Charge Injection Differential Sense Amplifier	P2003-119280	
100111620	3 CN		Resistive Cross Point Memory Arrays Having A Charge Injection Differential Sense Amplifier	03124128.X	1455412
100111620	4 KR		Resistive Cross Point Memory Arrays Having A Charge Injection Differential Sense Amplifier	2003-0026958	
100111621	1 US	6574129	Resistive Cross Point Memory Cell Arrays Having A Cross-couple Latch Sense Amplifier	10/136976	
100111621	2 JP		Resistive Cross Point Memory Cell Arrays Having A Cross-couple Latch Sense Amplifier	P2003-119281	
100111621	3 CN		Resistive Cross Point Memory Cell Arrays Having A Cross-couple Latch Sense Amplifier	03107765.X	1455414
100111621	4 KR		Resistive Cross Point Memory Cell Arrays Having A Cross-couple Latch Sense Amplifier	2003-0027212	
100200118	1 US	6842389	SYSTEM FOR AND METHOD OF FOUR-CONDUCTOR MAGNETIC RANDOM ACCESS MEMORY CELL AND DECODING SCHEME	10/346700	20040141365
100200118	3 CN		SYSTEM FOR AND METHOD OF FOUR-CONDUCTOR MAGNETIC RANDOM ACCESS MEMORY CELL AND DECODING SCHEME	0310123921.9	1538452
100200121	2 JP		MRAM Having Two Write Conductors	P2003-403010	
100200121	3 DE		MRAM Having Two Write Conductors	10342359.1	10342359
100200121	4 US	7102918	MRAM Having Two Write Conductors	10/983776	20050083732
100200219	1 US	6740947	MRAM With Asymmetric Cladded Conductor	10/293350	20040089904
100200219	2 JP		MRAM With Asymmetric Cladded Conductor	P2003-379703	
100200219	3 CN		MRAM With Asymmetric Cladded Conductor	03154091.0	1527319

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
100200219	4 TW	I240272	MRAM With Asymmetric Cladded Conductor	92115708	240272
100200450	1 US	6760016	An Integrated Digitizing Tablet And Color Display Apparatus And Method Of Operation	10/037028	20030122788
100200451	1 US	6665205	A Shared Global Word Line Magnetic Random Access Memory	10/079311	20030156444
100200451	3 CN		A Shared Global Word Line Magnetic Random Access Memory	03106026.9	1440037
100200451	4 KR		A Shared Global Word Line Magnetic Random Access Memory	2003-0010239	
100200451	7 US	6927092	A Shared Global Word Line Magnetic Random Access Memory	10/656758	20040047213
100200451	8 DE	60300950.6	A Shared Global Word Line Magnetic Random Access Memory	03250993.7	1339067
100200451	9 GB	1339067	A Shared Global Word Line Magnetic Random Access Memory	03250993.7	1339067
100200602	1 US	6791865	Memory Device Capable Of Calibration And Calibration Methods Therefor	10/232363	20040042262
100200602	3 CN		Memory Device Capable Of Calibration And Calibration Methods Therefor	03136379.2	1487525
100200602	5 EP	1403874	Memory Device Capable Of Calibration And Calibration Methods Therefor	03255479.2	1403874
100200602	6 US	6791874	Memory Device Capable Of Calibration And Calibration Methods Therefor	10/753298	20040141370
100200602	7 DE	60301112.8	Memory Device Capable Of Calibration And Calibration Methods Therefor	03255479.2	1403874
100200602	8 GB	1403874	Memory Device Capable Of Calibration And Calibration Methods Therefor	03255479.2	1403874
100200700	1 US	6791867	Selection Of Memory Cells In Data Storage Devices	10/299542	20040095802
100200700	4 TW		Selection Of Memory Cells In Data Storage Devices	92115827	
100200780	1 US	6903909	FERROMAGNETIC LAYER FOR MAGNETORESISTIVE ELEMENT	10/285815	20040085687
100200780	3 CN		FERROMAGNETIC LAYER FOR MAGNETORESISTIVE ELEMENT	03152518.0	1499520
100200780	5 TW		FERROMAGNETIC LAYER FOR MAGNETORESISTIVE ELEMENT	92113843	200408151
100200780	6 HK		FERROMAGNETIC LAYER FOR MAGNETORESISTIVE ELEMENT	04107449.8	1064795A
100201070	1 US	6788605	Shared Volatile And Non-volatile Memory	10/195818	20040008542
100201070	3 CN		Shared Volatile And Non-volatile Memory	03136045.9	1495899
100201070	6 US	6894918	Shared Volatile And Non-volatile Memory	10/697367	
100201070	7 HK		Shared Volatile And Non-volatile Memory	04107007.2	1064508A
100201306	1 US	6987692	Magnetic Memory Having Angled Third Conductor	10/678555	20050073882
100201306	2 DE		Magnetic Memory Having Angled Third Conductor	102004025662.4	102004025662

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
100201306	3 NL		Magnetic Memory Having Angled Third Conductor	1027124	
100201678	1 US	6674679	ADJUSTABLE CURRENT MODE DIFFERENTIAL AMPLIFIER FOR MULTIPLE BIAS POINT SENSING OF MRAM HAVING EQUI-POTENTIAL ISOLATION	10/262051	
100201679	1 US	6754123	Adjustable Current Mode Differential Amplifier For Multiple Bias Point Sensing Of MRAM Having Diode Isolation	10/261532	20040062117
100201680	1 US	6590804	ADJUSTABLE CURRENT MODE DIFFERENTIAL AMPLIFIER	10/198278	
100201680	2 JP		ADJUSTABLE CURRENT MODE DIFFERENTIAL AMPLIFIER	P2003-272462	
100201680	3 CN		ADJUSTABLE CURRENT MODE DIFFERENTIAL AMPLIFIER	03123820.3	
100201680	4 TW		ADJUSTABLE CURRENT MODE DIFFERENTIAL AMPLIFIER	92103303	
100201879	1 US	6891768	Power-Saving Reading Of Magnetic Memory Devices	10/293027	20040090852
100201879	2 SG	111120	Power-Saving Reading Of Magnetic Memory Devices	200303862.7	
100202306	1 US	7116576	Sensing A State Of A Storage Cell Including A Magnetic Element	10/957058	20050041517
100202307	1 US	6980477	Chopper Sensor For MRAM	10/314111	20040109345
100202546	1 US	6804145	A Memory Cell Sensing System And Method	10/286081	20040085794
100202550	1 US	6879534	A Method And System For Minimizing Differential Amplifier Power Supply Sensitivity	10/286577	20040085122
100202550	3 US	7023277	A Method And System For Minimizing Differential Amplifier Power Supply Sensitivity	11/129115	
100202552	1 US	6781906	A Memory Cell Sensing Integrator	10/299501	20040095827
100202554	1 US	6765834	A System And Method For Sensing Memory Cells Of An Array Of Memory Cells	10/299288	20040095826
100202730	1 US	6894938	System And Method Of Calibrating A Read Circuit In A Magnetic Memory	10/678322	20050073890
100202730	2 EP		System And Method Of Calibrating A Read Circuit In A Magnetic Memory	04255360.2	1526549
100202730	3 TW		System And Method Of Calibrating A Read Circuit In A Magnetic Memory	93108849	200514081
100202856	1 US	6740948	Magnetic Shielding For Reducing Magnetic Interference	10/233110	20040041218
100202964	1 US	6713396	Method Of Fabricating High Density Sub-Lithographic Features On A Substrate	10/135900	20030203636
100202964	2 JP		Method Of Fabricating High Density Sub-lithographic Features On A Substrate	P2003-084870	
100202964	4 KR		Method Of Fabricating High Density Sub-lithographic Features On A Substrate	2003-0026662	
100202964	6 EP		Method Of Fabricating High Density Sub-lithographic Features On A Substrate	03252668.3	1359613
100203735	1 US	6667901	Dual-Junction Magnetic Memory Device And Read Method	10/426381	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
100203735	2 JP		Dual-junction Magnetic Memory Device And Read Method	P2004-131047	
100203976	1 US	6839270	System For And Method Of Accessing A Four-conductor Magnetic Random Access Memory	10/346494	20040141364
100203976	2 JP		System For And Method Of Accessing A Four-conductor Magnetic Random Access Memory	P2004-010656	
100204424	1 US	6956762	Method And System For Data Communication On A Chip	10/444477	20040233710
100204424	2 JP		Method And System For Data Communication On A Chip	P2004-144306	
100204424	3 DE		Method And System For Data Communication On A Chip	102004004885.1	102004004885
100204424	4 IT		Method And System For Data Communication On A Chip	RM2004A000257	
100204424	5 US	7142448	Method And System For Data Communication On A Chip	11/211986	20050281078
100204426	1 US	7027318	Method And System For Adjusting Offset Voltage	10/449572	20040240256
100205213	1 US	6756239	Method For Constructing A Magneto-Resistive Element	10/414325	
200205266	1 US		Logical Data Block, Magnetic Random Access Memory, Memory Module, Computer System And Method	10/635150	20050030799
200205266	2 DE		Logical Data Block, Magnetic Random Access Memory, Memory Module, Computer System And Method	102004015526.7	102004015526
200205266	3 JP		Logical Data Block, Magnetic Random Access Memory, Memory Module, Computer System And Method	P2004-226547	
200205266	4 TW		Logical Data Block, Magnetic Random Access Memory, Memory Module, Computer System And Method	93102811	200506936
200205269	1 US	6826086	Method, Apparatus And System For Erasing And Writing A Magnetic Random Access Memory	10/635405	
200205270	1 US	6751147	Method For Adaptiely Writing A Magnetic Random Access Memory	10/635399	
200205270	2 DE		Method For Adaptiely Writing A Magnetic Random Access Memory	102004015555.0	102004015555
200205275	1 US	6930914	Methods For Isolating Memory Elements Within An Array	10/425362	20040218419
200205282	1 US	6847544	Magnetic Memory Which Detects Changes Between First And Second Resistive States Of A Memory Cell	10/689144	
200205282	2 DE		Magnetic Memory Which Detects Changes Between First And Second Resistive States Of A Memory Cell	102004030591.9	102004030591
200205286	1 US	7050326	Magnetic Memory Device With Current Carrying Reference Layer	10/680451	20050073883
200205286	3 JP		Magnetic Memory Device With Current Carrying Reference Layer	P2004-293901	
200205288	1 US	6961263	Memory Device With A Thermally Assisted Write	10/657519	20050052902
200205501	1 US	7027319	Retrieving Data Stored In A Magnetic Integrated Memory	10/465714	20040257862

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
200205501	2 JP		Retrieving Data Stored In A Magnetic Integrated Memory	P2004-180563	
200205501	3 TW		Retrieving Data Stored In A Magnetic Integrated Memory	93101984	200502960
200205501	4 DE		Retrieving Data Stored In A Magnetic Integrated Memory	102004008218.9	102004008218
200205508	1 US	6707710	Magnetic Memory Device With Larger Reference Cell	10/318520	
200205508	2 DE		Magnetic Memory Device With Larger Reference Cell	10338729.3	10338729
200205516	1 US	6990012	Magnetic Memory Device	10/680464	20050073880
200205974	1 US	7056749	A Simplified Magnetic Memory Cell	10/378210	20040175846
200205977	1 US	6785160	A Method Of Providing Stability Of A Magnetic Memory Cell	10/425352	
200205977	2 JP		A Method Of Providing Stability Of A Magnetic Memory Cell	P2004-131048	
200205977	3 CN		A Method Of Providing Stability Of A Magnetic Memory Cell	200410003527.6	1571066
200205977	4 TW		A Method Of Providing Stability Of A Magnetic Memory Cell	92129804	
200205978	1 US	6950919	Computer System With Operating System Permitting Dynamic Adjustment Of Main Memory	10/397434	20040193783
200205978	2 JP		Computer System With Operating System Permitting Dynamic Adjustment Of Main Memory	P2004-077827	*
200205980	1 US	6927995	Multi-bit MRAM Device With Switching Nucleation Sites	10/449261	20030209769
200205980	2 US	7078244	Multi-bit MRAM Device With Switching Nucleation Sites	11/112815	20050195649
200206155	1 US	7079436	Resistive Cross Point Memory	10/675740	20050078536
200206155	2 DE		Resistive Cross Point Memory	102004025422.2	102004025422
200206155	3 JP		Resistive Cross Point Memory	P2004-283067	
200206392	1 US	6803274	MAGNETIC MEMORY CELL HAVING AN ANNULAR DATA LAYER AND A SOFT REFERENCE LAYER	10/233109	20040043562
200206392	2 US	6903403	MAGNETIC MEMORY CELL HAVING AN ANNULAR DATA LAYER AND A SOFT REFERENCE LAYER	10/902925	20050014320
200206394	1 US	6808940	Magnetic Shielding For Reducing Magnetic Interference	10/232209	20040043516
200206394	2 US	6867468	Magnetic Shielding For Reducing Magnetic Interference	10/440279	20040043519
200206475	1 US	6979998	A Magnetic Filter	10/417054	
200206997	1 US	7054119	Coupled Ferromagnetic Systems Having Modified Interfaces	10/463930	20040257717
200207329	1 US	6989975	Magnetoresistive Device Including Pinned Structure	10/463993	20040257718

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no	
200207356	1 US	6901005	Method And System Reading Magnetic Memory	10/649752	20050047201	
200207356	2 DE		Method And System Reading Magnetic Memory	04020258.3	102004020258	
200207356	3 JP		Method And System Reading Magnetic Memory	P2004-247698		
200207356	4 TW		Method And System Reading Magnetic Memory	93105123	200509127	
200208227	1 US	7009872	MRAM Storage Device	10/743665	20050162897	
200208229	1 US	6842364	Memory Cell Strings In A Resistive Cross Point Memory Cell Array	10/614505	20050007825	
200208229	2 DE		Memory Cell Strings In A Resistive Cross Point Memory Cell Array	102004011419.6	102004011419	*
200208229	3 JP		Memory Cell Strings In A Resistive Cross Point Memory Cell Array	P2004-195174		*
200208506	1 US	6865108	Memory Cell Strings In A Resistive Cross Point Memory Cell Array	10/614581	20050007823	
200208506	2 DE		Memory Cell Strings In A Resistive Cross Point Memory Cell Array	102004011425.0	102004011425	
200208506	3 KR		Memory Cell Strings In A Resistive Cross Point Memory Cell Array	2004-0052189		
200208513	1 US		Magnetic Shielding For Magnetic Random Access Memory	10/631404	20040150091	
200208921	1 US	7136300	Magnetic Memory Device Including Groups Of Series-connected Memory Elements	10/680483	20050073881	
200208921	3 JP		Magnetic Memory Device Including Groups Of Series-connected Memory Elements	P2004-292275		
200208959	1 US	6836422	System And Method For Reading A Memory Cell	10/614504	20050007829	
200208959	2 DE		System And Method For Reading A Memory Cell	102004011418.8	102004011418	
200208959	3 KR		System And Method For Reading A Memory Cell	2004-0052269		
200208961	1 US	7191379	Magnetic Memory With Error Correction Coding	10/659630	20050055621	
200208961	2 DE		Magnetic Memory With Error Correction Coding	102004023821.9	102004023821	
200208962	1 US		Assisted Memory Device With Integrated Cache	10/621632	20050013181	
200208963	1 US	7149950	Assisted Memory Device	10/661937	20050060628	
200208967	1 US	6862211	Magneto-Resistive Memory Device	10/614230	20050007815	
200209237	1 US	6936903	A MAGNETIC MEMROY CELL HAVING A SOFT REFERENCE LAYER	10/692546	20040092039	
200209237	3 JP		A MAGNETIC MEMROY CELL HAVING A SOFT REFERENCE LAYER	P2004-309436		
200209239	1 US		Heating MRAM Cells To Ease State Switching	10/698501	20050094456	
200209239	2 CN		Heating MRAM Cells To Ease State Switching	200410090531.0	1612263	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no	
200209239	3 DE		Heating MRAM Cells To Ease State Switching	102004033159.6	102004033159	
200209239	4 JP		Heating MRAM Cells To Ease State Switching	P2004-313278		
200209239	5 TW		Heating MRAM Cells To Ease State Switching	93113463	200515418	
200209240	1 US	7186571	Method Of Fabricating Compositionally Modulated Electrode In A Magnetic Tunnel Junction Device (amended)	10/769107	20050170533	
200209241	1 US	6984530	Method Of Fabricating A MRAM Device	10/811553	20050214953	
200209347	1 US	6828260	Ultra-Violet Treatment Of A Tunnel Barrier Layer Through An Overlayer In A Tunnel Junction Device	10/282670	20040082201	
200209347	2 JP		Ultra-Violet Treatment Of A Tunnel Barrier Layer Through An Overlayer In A Tunnel Junction Device	P2003-347960		
200209347	3 CN		Ultra-Violet Treatment Of A Tunnel Barrier Layer Through An Overlayer In A Tunnel Junction Device	03155636.1	1501458	*
200209347	5 EP		Ultra-Violet Treatment Of A Tunnel Barrier Layer Through An Overlayer In A Tunnel Junction Device	03256453.6	1416495	
200209347	6 HK		Ultra-Violet Treatment Of A Tunnel Barrier Layer Through An Overlayer In A Tunnel Junction Device	04108386.1	1065642A	*
200209353	1 US	6980466	SOFT-REFERENCE FOUR CONDUCTOR MAGNETIC MEMORY STORAGE DEVICE	10/758658	20050157540	
200209353	2 DE		SOFT-REFERENCE FOUR CONDUCTOR MAGNETIC MEMORY STORAGE DEVICE	102004060645.5	102004060645	
200209353	3 JP		SOFT-REFERENCE FOUR CONDUCTOR MAGNETIC MEMORY STORAGE DEVICE	P2005-007050		
200209575	1 US		A Method Of Making A Magnetic Tunnel Junction Device (AMENDED)	10/692612		*
200209575	2 US	6998662	A Method Of Making A Magnetic Tunnel Junction Device (AMENDED)	11/080092	20050156215	
200300153	1 US	7041598	Directional Ion Etching Process For Patterning Self-Aligned Via Contracts	10/606263	20040266179	
200300378	1 US	6794697	Asymmetric Patterned Magnetic Memory	10/677394		
200300378	3 JP		Asymmetric Patterned Magnetic Memory	P2004-281345		
200300378	4 US	6921954	Asymmetric Patterned Magnetic Memory	10/932693	20050073016	
200300488	1 US	6807118	An Adjustable Offset Differential Amplifier	10/350398		
200300488	4 TW		An Adjustable Offset Differential Amplifier	92120980		
200300565	1 US		MOLECULAR OPTOELECTRONIC MEMORY DEVICE	10/721574	20050111341	
200300565	5 TW		MOLECULAR OPTOELECTRONIC MEMORY DEVICE	93118075		*
200300753	1 US	6906941	A Stacked Magnetic Memory Structure	10/624175	20050018475	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
200300753	2 US	7196957	Magnetic Memory Structure Using Heater Lines To Assist In Writing Operations (as Amended)	11/105054	20050185453
200308742	1 US	7180770	Series Diode Thermally Assisted MRAM	11/089688	20060215444
200308743	1 US		Using Sense Lines To Thermally Control The State Of An MRAM (as Amended)	10/733089	20050128801
200308744	1 US	6930369	A Thin Film Device And A Method Of Providing Thermal Assistance Therein	10/713510	20050104146
200308748	1 US	6819586	THERMALLY-ASSISTED MAGNETIC MEMORY STRUCTURES	10/692841	
200308748	3 JP		THERMALLY-ASSISTED MAGNETIC MEMORY STRUCTURES	P2004-306382	
200308749	1 US	6839271	A Magnetic Memory Device	10/685618	
200308750	1 US	6937506	A Magnetic Memory Device	10/753539	20050152182
200308751	1 US	7057920	Two Conductor Thermally Assisted Magnetic Memory	10/832912	20050237795
200308752	1 US	7102921	A Magnetic Memory Device	10/843787	20050254292
200308998	1 US	7102920	Soft Reference Three Conductor Magnetic Memory Storage Device	10/806709	20050213375
200308998	2 EP		Soft Reference Three Conductor Magnetic Memory Storage Device	05251318.1	1580758
200308998	3 CN		Soft Reference Three Conductor Magnetic Memory Storage Device	200510063759.5	1674148
200308998	4 JP		Soft Reference Three Conductor Magnetic Memory Storage Device	P2005-081090	
200308998	5 TW		Soft Reference Three Conductor Magnetic Memory Storage Device	94105410	
200310027	1 US	6956271	Switching Of Soft Referenced Layers Of Magnetic Memory Devices	10/776580	
200310030	1 US	6885582	MAGNETIC MEMORY STORAGE DEVICE	10/460816	
200310030	2 JP		MAGNETIC MEMORY STORAGE DEVICE	P2004-171187	
200310030	4 US	6977839	Magnetic Memory Storage Device	11/064883	20050139883
200310067	1 US	6850430	Regulating A Magnetic Memory Cell Write Current	10/725746	
200310067	3 CN		Regulating A Magnetic Memory Cell Write Current	200410100129.6	1627434
200310067	4 JP		Regulating A Magnetic Memory Cell Write Current	P2004-349800	
200310067	5 TW	1256055	Regulating A Magnetic Memory Cell Write Current	93117656	200519960
200310068	1 US		A Current Threshold Detector	10/767428	20050169059
200310068	3 CN		A Current Threshold Detector	200510006711.0	1649029
200310068	4 JP		A Current Threshold Detector	P2005-013730	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no	
200310068	5 TW		A Current Threshold Detector	93122269		
200310138	1 US	6791873	AN APPARATUS AND METHOD FOR GENERATING A WRITE CURRENT FOR A MAGNETIC MEMORY CELL	10/658442		
200310138	3 JP		AN APPARATUS AND METHOD FOR GENERATING A WRITE CURRENT FOR A MAGNETIC MEMORY CELL	P2004-254134		
200310247	1 US	6865105	THERMAL-ASSISTED SWITCHING ARRAY CONFIGURATION FOR MRAM	10/668405	20050063223	
200310247	3 JP		THERMAL-ASSISTED SWITCHING ARRAY CONFIGURATION FOR MRAM	P2004-271362		
200310251	1 US	7079438	Controlled Temperature, Thermal-assisted Magnetic Memory Device	10/779909	20050180238	
200310251	2 DE		Controlled Temperature, Thermal-assisted Magnetic Memory Device	102005002526.9	102005002526	
200310251	4 CN		Controlled Temperature, Thermal-assisted Magnetic Memory Device	200510009079.5	1658326	
200310251	5 JP		Controlled Temperature, Thermal-Assisted Magnetic Memory Device	P2005-031749		
200310251	6 TW	1255459	Controlled Temperature, Thermal-assisted Magnetic Memory Device	93124963	1255459	
200310817	1 US		Data Storage Device Including Conductive Probe And Ferroelectric Storage Medium	10/698717	20050094430	
200310817	2 GB		Data Storage Device Including Conductive Probe And Ferroelectric Storage Medium	0423671.7	2407694	*
200310817	3 JP		Data Storage Device Including Conductive Probe And Ferroelectric Storage Medium	P2004-313279		
200311028	1 US		An Optical Signal Transmission Transducer	10/414927		
200311200	1 US	6980455	Remote Sensed Pre-amplifier For Cross Point Arrays	10/770675	20050169034	
200311201	1 US		Analog Preamplifier Calibration	11/266861		
200311401	1 US		Digital Current Source	11/267705		
200311702	1 US		MULTI-SAMPLE READ CIRCUIT HAVING TEST MODE OF OPERATION	10/698896	20050102576	
200311702	3 JP		MULTI-SAMPLE READ CIRCUIT HAVING TEST MODE OF OPERATION	P2004-313338		
200311703	1 US	7102948	A Resistance Change Sensor	10/816482	20050226034	
200311703	2 DE		A Resistance Change Sensor	102005009546.1	102005009546	
200311703	3 CN		A Resistance Change Sensor	200510065144.6	1681041	
200311703	4 JP		A Resistance Change Sensor	P2005-105833		
200311703	5 TW		A Resistance Change Sensor	94106033		
200311824	1 US	7203265	Synchronous Counting Circuit	11/155523	20060288059	
200312363	1 US	7027323	Storage Device Having Parallel Connected Memory Cells That Include Magnetoresistive	10/817462	20050226071	

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title Elements	appl_no	publication_no
200312772	1 US	6819587	Thermal-assisted Nanotip Magnetic Memory Storage Device	10/460785	
200313529	1 US		An Input Device Including A Layer Of Particles	10/831110	20050237309
200313717	1 US	6925003	A Magnetic Memory Cell Structure	10/658158	20050052905
200314474	1 US		PROGRAMMING OF PROGRAMMABLE RESISTIVE MEMORY DEVICES	10/933039	20060044878
200314474	2 DE		PROGRAMMING OF PROGRAMMABLE RESISTIVE MEMORY DEVICES	102005036555.8	102005036555
200314474	3 JP		PROGRAMMING OF PROGRAMMABLE RESISTIVE MEMORY DEVICES	P2005-255038	
200314755	1 US		SILVER ISLAND ANTI-FUSE	10/914255	20060028895
200314755	2 DE		SILVER ISLAND ANTI-FUSE	102005032280.8	102005032280
200314755	3 JP		SILVER ISLAND ANTI-FUSE	P2005-230716	
200315044	1 US	6937504	Selecting A Magnetic Memory Cell Write Current	10/725803	20050117409
200315765	1 US		RF Field Heated Diodes For Providing Thermally Assisted Switching Of Magnetic Memory Elements	11/034418	20060163629
200315765	2 DE		RHfield Heated Diodes For Providing Thermally Assisted Switching Of Magnetic Memory Elements	102005059556.1	
200315765	3 JP		RHfield Heated Diodes For Providing Thermally Assisted Switching Of Magnetic Memory Elements	P2006-003312	
200315768	1 US	7009903	Sense Amplifying Magnetic Tunnel Device	10/855042	20050276097
200315878	1 US	6940747	A MAGNETIC MEMORY DEVICE	10/854858	
200315897	1 US	7042757	1R1D MRAM Block Architecture	10/794302	20050195647
200315897	2 DE		1R1D MRAM Block Architecture	102005005584.2	102005005584
200315897	3 JP		1R1D MRAM Block Architecture	P2005-041746	
200316175	1 US	6982909	System And Method For Reading A Memory Cell	10/765483	
200316175	2 DE		System And Method For Reading A Memory Cell	102004039236.6	102004039236
200316175	3 KR		System And Method For Reading A Memory Cell	2005-0007405	
200316175	4 US		System And Method For Reading A Memory Cell	11/252143	20060039191
200316177	1 US	6914809	Memory Cell Strings	10/765484	
200316177	2 DE		Memory Cell Strings	102004039235.8	102004039235

CONFIDENTIAL

HP Identification #	cc	patent_no	HP Internal Title	appl_no	publication_no
200316178	1 US	6958933	Memory Cell Strings	10/784514	
200316178	2 DE		Memory Cell Strings	102004060710.9	
200316178	3 KR		Memory Cell Strings	2005-0014640	
200400408	1 US		Multi-Layered Magnetic Memory Structures	11/285991	
200400659	1 US	7130235	Method And Apparatus For A Sense Amplifier	10/934719	20060050582
200400672	1 US		Method And Apparatus For Multi-Plane MRAM	10/934243	20060050552
200400838	1 US		A Process For Forming Magnetic Memory Structures	11/118828	
200400839	1 US		Multi-Layered Magnetic Memory Structures	11/286245	
200400840	1 US	7138341	A Process For Making A Memory Structure	10/886963	
200401513	1 US		A Thin Film Device And A Method Of Formation Thereof	10/934922	20060043444
200401516	1 US		Multi-Layered Magnetic Memory Structures	11/286009	
200402658	1 US	7002197	Cross Point Resistive Memory Array	10/814094	20050161715
200500616	1 US	7145797	Selecting A Magnetic Memory Cell Write Current	11/003904	20050117412
200503200	1 US		Controllably Connectable Strings Of MRAM Cells	11/264539	
300111209	1 US	7149949	Method For Error Correction Decoding In A Magnetoresistive Solid-state Storage Device	10/093841	03/0023927